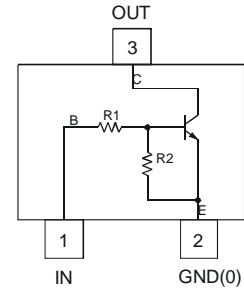




DDTD (xxxx) U NPN PRE-BIASED 500 mA SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDTB)
- Built-In Biasing Resistors, R1, R2
- **Lead Free/RoHS Compliant Version (Note 2)**
- "Green" Device, Note 3 and 4



| P/N | R1 (NOM) | R2 (NOM) | MARKING |
|-----------|----------|----------|---------|
| DDTD113EU | 1K | 1K | N60 |
| DDTD123EU | 2.2K | 2.2K | N61 |
| DDTD143EU | 4.7K | 4.7K | N62 |
| DDTD114EU | 10K | 10K | N63 |
| DDTD122JU | 0.22K | 4.7K | N64 |
| DDTD113ZU | 1K | 10K | N65 |
| DDTD123YU | 2.2K | 10K | N66 |
| DDTD133HU | 3.3K | 10K | N67 |
| DDTD123TU | 2.2K | OPEN | N69 |
| DDTD143TU | 4.7K | OPEN | N70 |
| DDTD114TU | 10K | OPEN | N71 |
| DDTD114GU | 0 | 10K | N72 |

Maximum Ratings @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Unit |
|--|-----------------------------------|---|------|
| Supply Voltage, (3) to (2) | V _{CC} | 50 | V |
| Input Voltage, (1) to (2) | V _{IN} | -10 to +10 -10 to +12 -10 to +30 -10 to +40 -5 to +5 -5 to +10 -5 to +12 -6 to +20 | V |
| Input Voltage, (2) to (1) | V _{EBO (MAX)} | 5 | V |
| Output Current | I _C | 500 | mA |
| Power Dissipation | P _d | 200 | mW |
| Thermal Resistance, Junction to Ambient Air (Note 1) | R _{θJA} | 625 | °C/W |
| Operating and Storage Temperature Range | T _j , T _{STG} | -55 to +150 | °C |

- Notes:
1. Mounted on FR4 PC Board with recommended pad layout
 2. No purposefully added lead.
 3. Diodes Inc.'s "Green" policy can be found on our
 4. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.



Electrical Characteristics @_{T_A} = 25°C unless otherwise specified

R1, R2 Types

| Characteristic | | Symbol | Min | Typ | Max | Unit | Test Condition |
|-------------------------|--|--------------|--|-----|--|---------|---------------------------------------|
| Input Voltage | DDTD113EU DDTD123EU DDTD143EU DDTD114EU DDTD122JU DDTD113ZU DDTD123YU DDTD133HU | $V_{I(off)}$ | 0.5 | — | — | V | $V_{CC} = 5V, I_O = 100\mu A$ |
| | DDTD113EU DDTD123EU DDTD143EU DDTD114EU DDTD122JU DDTD113ZU DDTD123YU DDTD133HU | | $V_{I(on)}$ | | | | |
| Output Voltage | | $V_{O(on)}$ | — | — | 0.3V | V | $I_O/I_I = 50mA/2.5mA$ |
| Input Current | DDTD113EU DDTD123EU DDTD143EU DDTD114EU DDTD122JU DDTD113ZU DDTD123YU DDTD133HU | I_I | — | — | 7.2 3.8 1.8 0.88 28 7.2 3.6 2.4 | mA | $V_I = 5V$ |
| Output Current | | $I_{O(off)}$ | — | — | 0.5 | μA | $V_{CC} = 50V, V_I = 0V$ |
| DC Current Gain | DDTD113EU DDTD123EU DDTD143EU DDTD114EU DDTD122JU DDTD113ZU DDTD123YU DDTD133HU | G_I | 33 39 47 56 47 56 56 56 | — | — | — | $V_O = 5V, I_O = 50mA$ |
| Gain-Bandwidth Product* | | f_T | — | 200 | — | MHz | $V_{CE} = 10V, I_E = 5mA, f = 100MHz$ |

* Transistor - For Reference Only

Electrical Characteristics @_{T_A} = 25°C unless otherwise specified

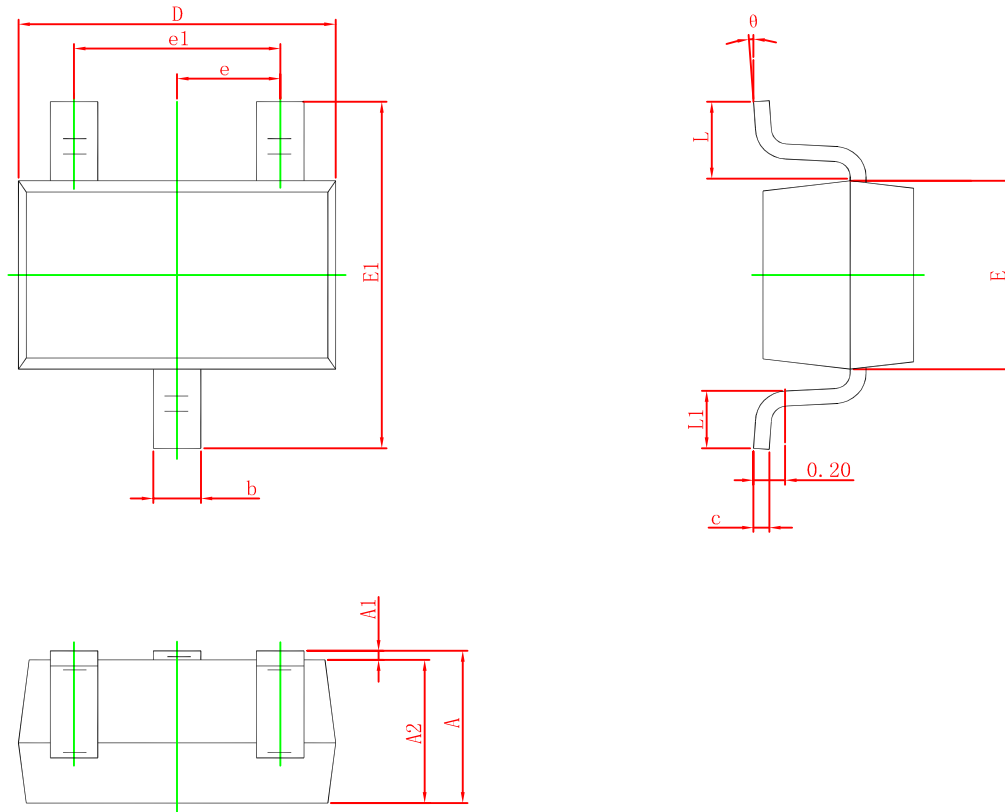
R1-Only, R2-Only Types

| Characteristic | | Symbol | Min | Typ | Max | Unit | Test Condition |
|--------------------------------------|--|---------------|-------------------------|------------------------|--------------------------|---------|---|
| Collector-Base Breakdown Voltage | | BV_{CBO} | 50 | — | — | V | $I_C = 50\mu A$ |
| Collector-Emitter Breakdown Voltage | | BV_{CEO} | 40 | — | — | V | $I_C = 1mA$ |
| Emitter-Base Breakdown Voltage | DDTD123TU DDTD143TU DDTD114TU DDTD114GU | BV_{EBO} | 5 | — | — | V | $I_E = 50\mu A$ $I_E = 50\mu A$ $I_E = 50\mu A$ $I_E = 720\mu A$ |
| Collector Cutoff Current | | I_{CBO} | — | — | 0.5 | μA | $V_{CB} = 50V$ |
| Emitter Cutoff Current | DDTD123TU DDTD143TU DDTD114TU DDTD114GU | I_{EBO} | — — — 300 | — | 0.5 0.5 0.5 580 | μA | $V_{EB} = 4V$ |
| Collector-Emitter Saturation Voltage | | $V_{CE(sat)}$ | — | — | 0.3 | V | $I_C = 50mA, I_B = 2.5mA$ |
| DC Current Transfer Ratio | DDTD123TU DDTD143TU DDTD114TU DDTD114GU | h_{FE} | 100 100 100 56 | 250 250 250 — | 600 600 600 — | — | $I_C = 5mA, V_{CE} = 5V$ |
| Gain-Bandwidth Product* | | f_T | — | 200 | — | MHz | $V_{CE} = 10V, I_E = -5mA, f = 100MHz$ |

* Transistor - For Reference Only



SOT-323 PACKAGE OUTLINE DIMENSIONS



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|----------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 0.900 | 1.100 | 0.035 | 0.043 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.000 | 0.035 | 0.039 |
| b | 0.200 | 0.400 | 0.008 | 0.016 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.000 | 2.200 | 0.079 | 0.087 |
| E | 1.150 | 1.350 | 0.045 | 0.053 |
| E1 | 2.150 | 2.450 | 0.085 | 0.096 |
| e | 0.650 TYP. | | 0.026 TYP. | |
| e1 | 1.200 | 1.400 | 0.047 | 0.055 |
| L | 0.525 REF. | | 0.021 REF. | |
| L1 | 0.260 | 0.460 | 0.010 | 0.018 |
| θ | 0° | 8° | 0° | 8° |